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(54) **DRIFT COMPENSATION FOR CODEWORDS IN MEMORY**

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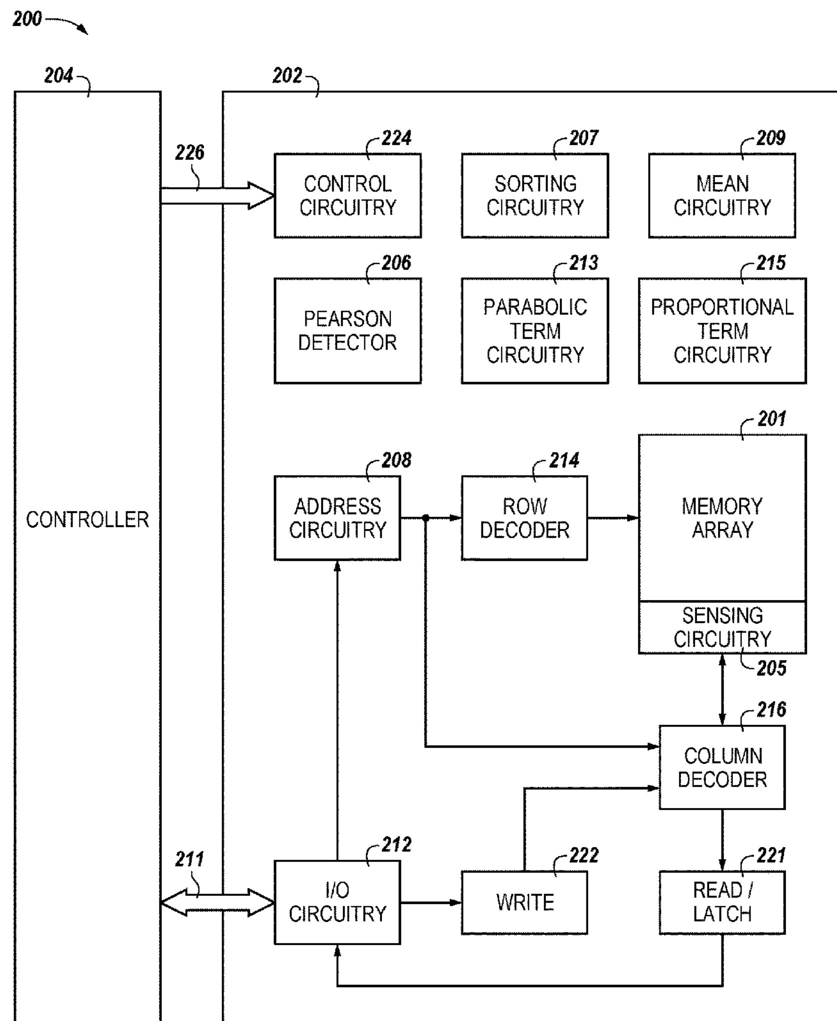
(57) **ABSTRACT**

Systems, methods, and apparatuses are provided for drift compensation for codewords in memory. A memory device comprises memory cells and circuitry configured to sense a codeword stored in the memory cells. The circuitry is further configured to determine a value of a cell metric of each memory cell of the sensed codeword, wherein the value of the cell metric of each of the memory cells is determined based on a summation of a threshold voltage value of each of the memory cells, a mean of the threshold voltage values of the memory cells, and a value proportional to the mean of the threshold voltage values of the memory cells. The circuitry is further configured to determine which cell metric of each of the memory cells has a lowest value, input that cell metric into a Pearson detector, and determine the originally programmed data of the codeword using the Pearson detector.



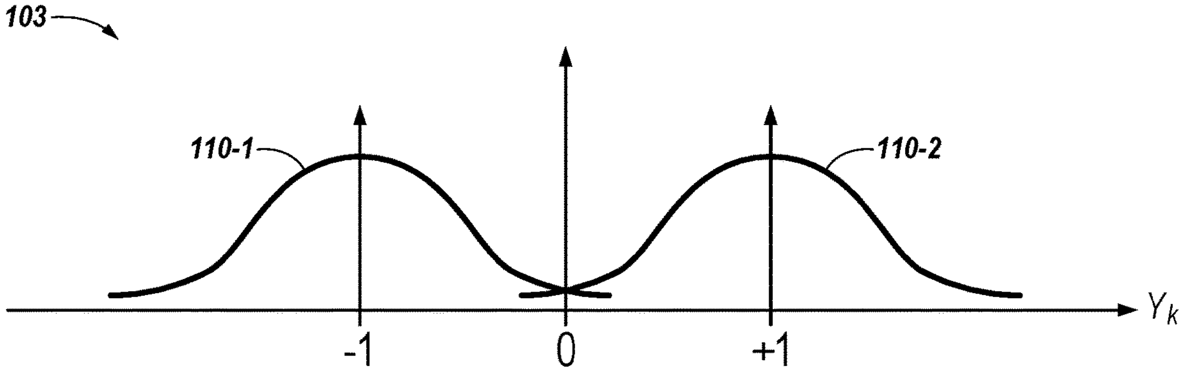


FIG. 1A

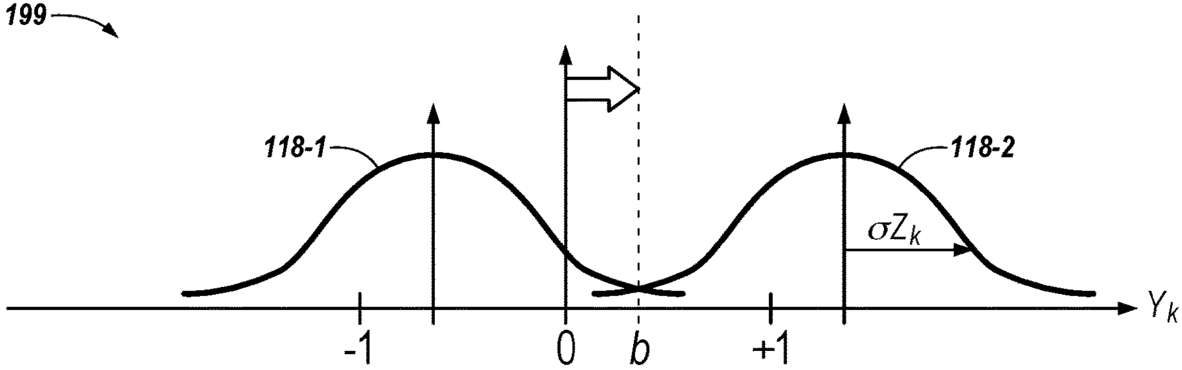


FIG. 1B

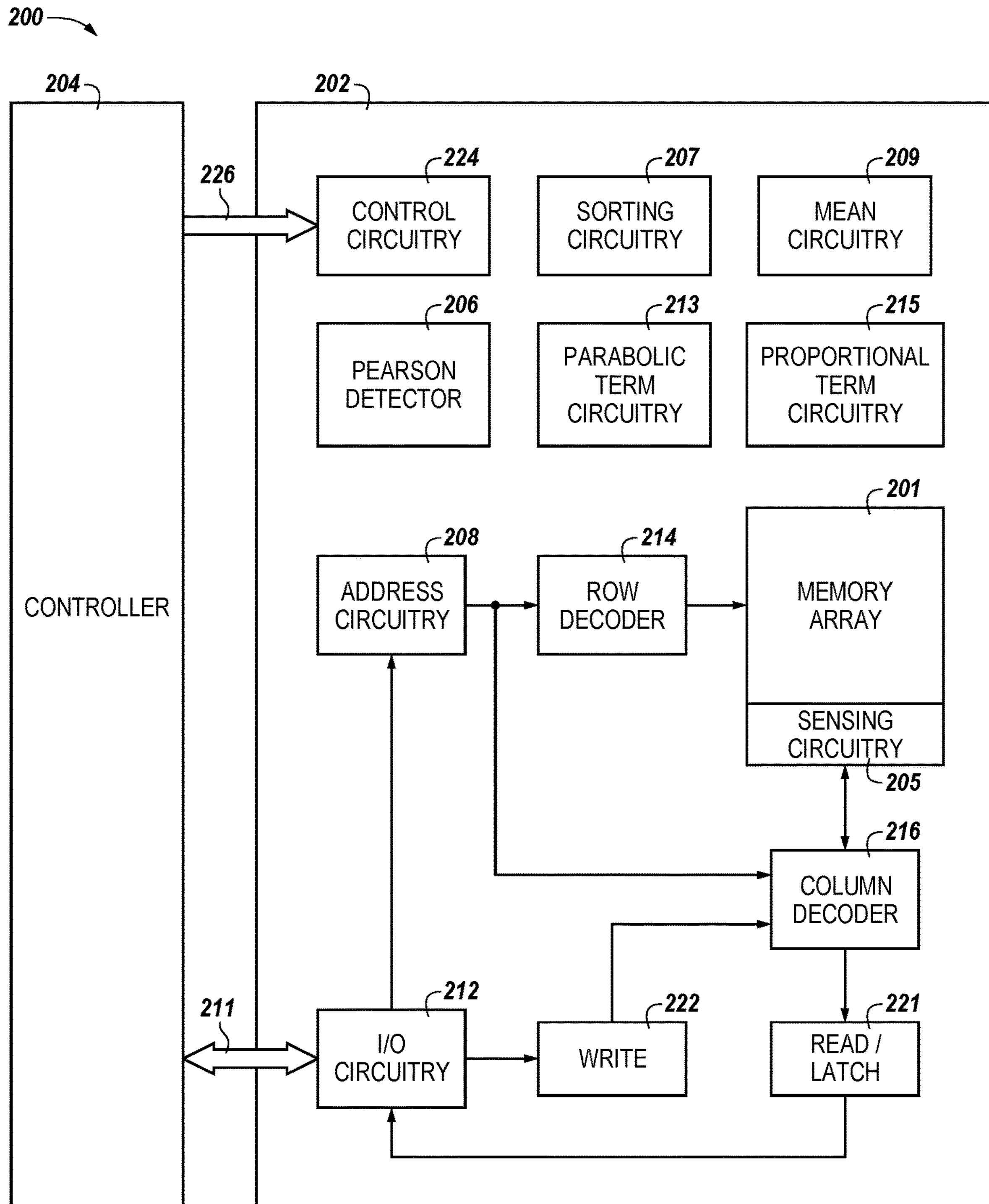


FIG. 2

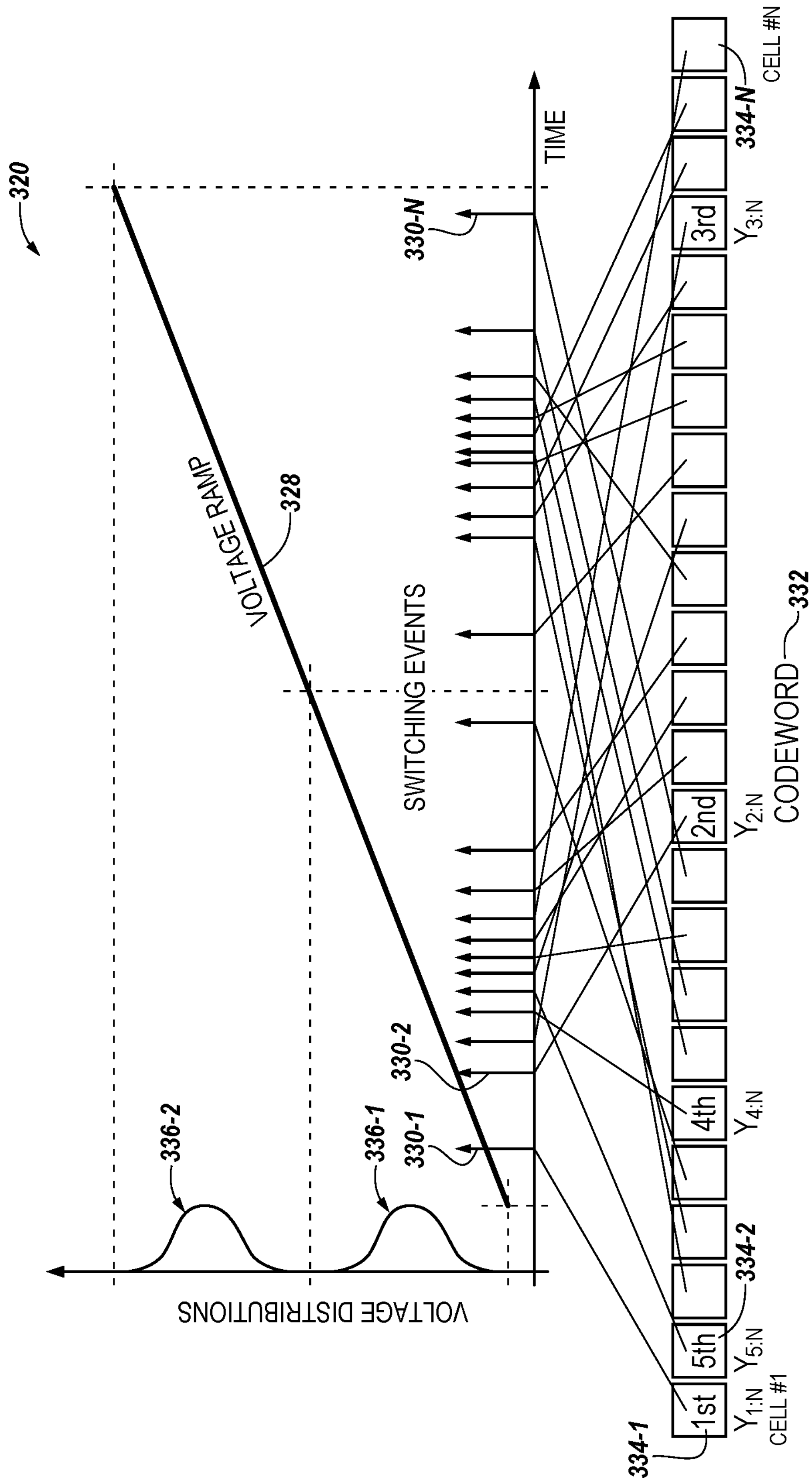


FIG. 3

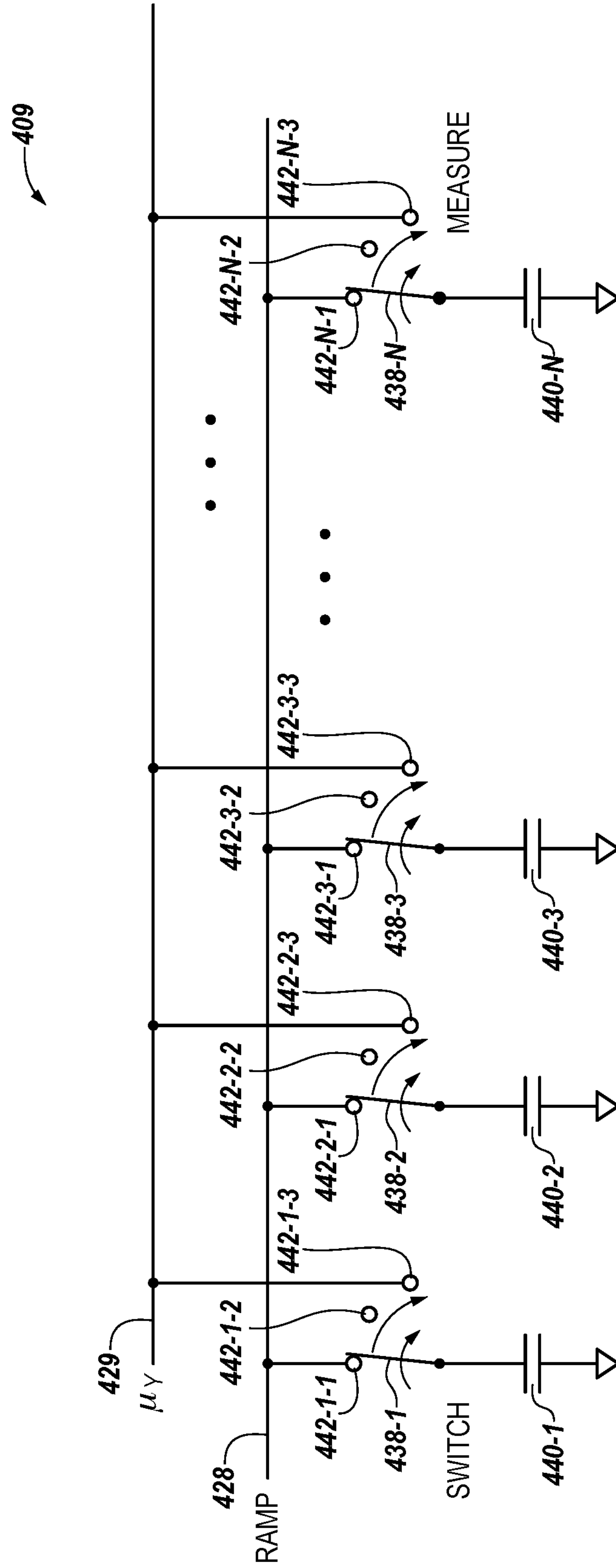


FIG. 4

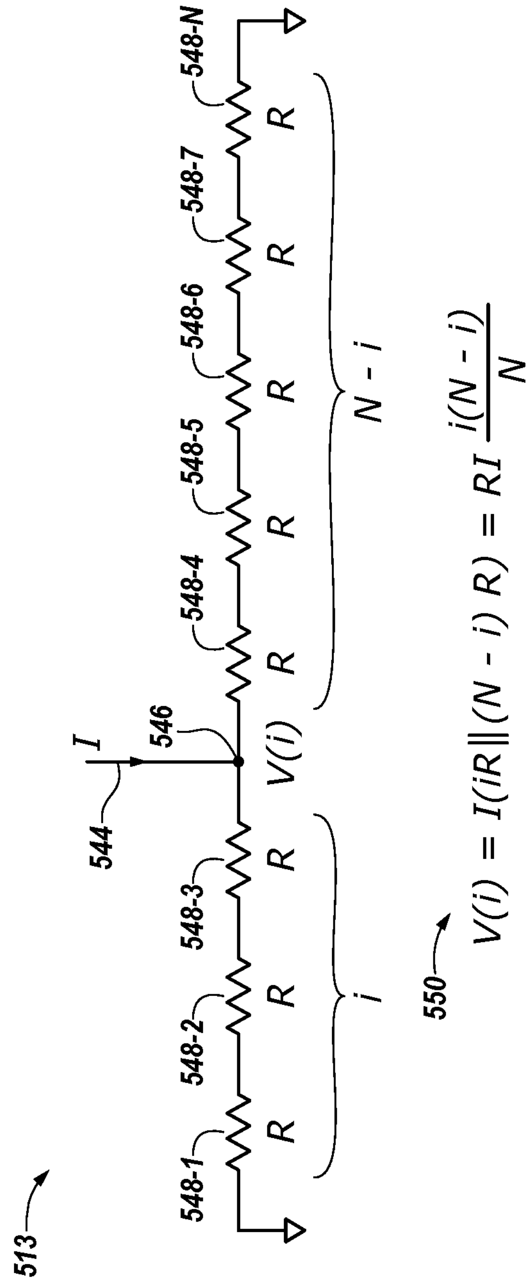


FIG. 5

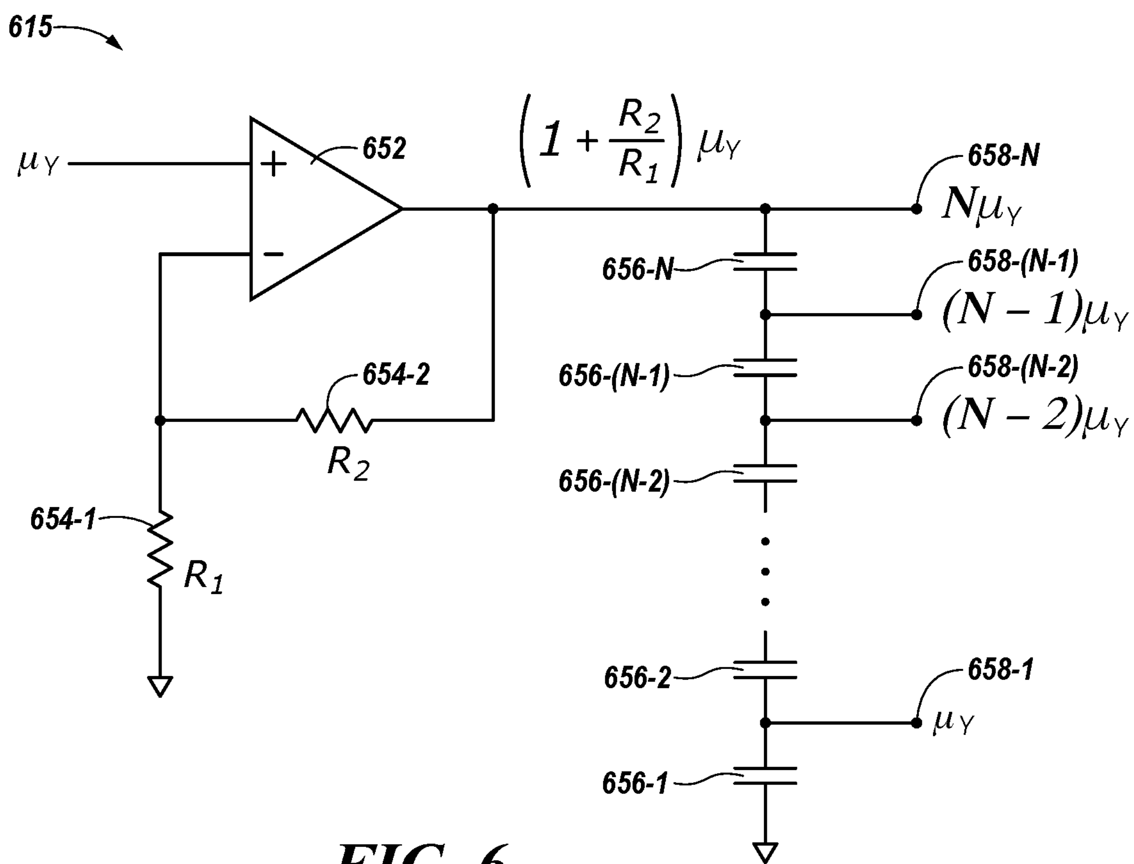


FIG. 6

DRIFT COMPENSATION FOR CODEWORDS IN MEMORY

PRIORITY INFORMATION

[0001] This application claims the benefit of U.S. Provisional Application Ser. No. 63/402,317 filed on Aug. 30, 2022, the contents of which are incorporated herein by reference.

TECHNICAL FIELD

[0002] The present disclosure relates generally to semiconductor memory and methods, and more particularly, to drift compensation for codewords in memory.

BACKGROUND

[0003] Memory devices are typically provided as internal, semiconductor, integrated circuits and/or external removable devices in computers or other electronic devices. There are many different types of memory including volatile and non-volatile memory. Volatile memory can require power to maintain its data and can include random-access memory (RAM), dynamic random access memory (DRAM), and synchronous dynamic random access memory (SDRAM), among others. Non-volatile memory can provide persistent data by retaining stored data when not powered and can include NAND flash memory, NOR flash memory, read only memory (ROM), and resistance variable memory such as phase change random access memory (PCRAM), resistive random access memory (RRAM), magnetic random access memory (MRAM), and programmable conductive memory, among others.

[0004] Memory devices can be utilized as volatile and non-volatile memory for a wide range of electronic applications in need of high memory densities, high reliability, and low power consumption. Non-volatile memory may be used in, for example, personal computers, portable memory sticks, solid state drives (SSDs), digital cameras, cellular telephones, portable music players such as MP3 players, and movie players, among other electronic devices.

[0005] Memory devices can include memory cells that can store data based on the charge level of a storage element (e.g., a capacitor) or can store data based on their conductivity state. Such memory cells can be programmed to store data corresponding to a target data state by varying the charge level of the storage element (e.g., different levels of charge of the capacitor may represent different data sates) or by varying the conductivity level of the storage element. For example, sources of an electrical field or energy, such as positive or negative electrical pulses (e.g., positive or negative voltage or current pulses), can be applied to the memory cell (e.g., to the storage element of the cell) for a particular duration to program the cell to a target data state.

[0006] A memory cell can be programmed to one of a number of data states. For example, a single level memory cell (SLC) can be programmed to a targeted one of two different data states, which can be represented by the binary units 1 or 0 and can depend on whether the capacitor of the cell is charged or uncharged. As an additional example, some memory cells can be programmed to a targeted one of more than two data states (e.g., 1111, 0111, 0011, 1011, 1001, 0001, 0101, 1101, 1100, 0100, 0000, 1000, 1010, 0010, 0110, and 1110). Such cells may be referred to as multi state memory cells, multiunit cells, or multilevel cells (MLCs). MLCs can provide higher density memories without increasing the number of memory cells since each cell can represent more than one digit (e.g., more than one data bit).

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] FIGS. **1**A and **1**B illustrate diagrams of a number of threshold voltage distributions, sensing voltages, and data assignments associated with a group of memory cells in accordance with an embodiment of the present disclosure.

[0008] FIG. **2** is a block diagram illustration of an example apparatus in accordance with an embodiment of the present disclosure.

[0009] FIG. **3** is a diagram illustrating voltage distributions and corresponding data bits in a codeword in accordance with an embodiment of the present disclosure.

[0010] FIG. **4** illustrates circuitry for determining the mean threshold voltage value of memory cells corresponding to data bits in a codeword in accordance with an embodiment of the present disclosure.

[0011] FIG. **5** illustrates circuitry for determining a parabolic term of a codeword in accordance with an embodiment of the present invention.

[0012] FIG. **6** illustrates circuitry for determining a term proportional to the mean threshold voltage value of memory cells corresponding to data bits in a codeword in accordance with an embodiment of the present invention.

DETAILED DESCRIPTION

[0013] The present disclosure includes apparatuses, methods, and systems for drift compensation for codewords in memory. An embodiment includes a memory device comprising an array of memory cells and circuitry configured to sense a codeword stored in the array of memory cells, determine a value of a cell metric of each memory cell of the sensed codeword, wherein the value of the cell metric of each of the memory cells is determined based on a summation of a threshold voltage value of each of the memory cells, a mean of the threshold voltage values of the memory cells, and a value proportional to the mean of the threshold voltage values of the memory cells. The circuitry is further configured to determine which cell metric of each of the memory cells has a lowest value, input the cell metric determined to have the lowest value to a Pearson detector, and determine originally programmed data of the codeword using the Pearson detector.

[0014] A memory device can address memory cells for operations (e.g., sense and program operations) in groups (e.g., packets) called words or codewords. As memory cells are sensed and programmed, their response to positive or negative electrical pulses can change cycle after cycle (e.g., according to a specific electrical bias history of the codeword to which they belong).

[0015] For example, when performing a sense operation (e.g., a read operation), a memory device may access a memory cell, which may output a signal to sense circuitry that can correspond to the data state of the memory cell (e.g., to a value stored by the memory cell). To determine the data state of the memory cell, the sense circuitry may compare the signal output by the memory cell to a reference signal, which may be, for instance, a reference voltage. The reference voltage may correspond to a voltage positioned between an expected voltage level of the signal output by a

memory cell programmed to a first data state (e.g., storing a first logic value) and an expected voltage level of the signal output by a memory cell programmed to a second data state (e.g., storing a second logic value). For instance, the sense circuitry may determine that the memory cell has been programmed to a first data state if the signal output by the memory cell is less than the reference voltage, and that the memory cell has been programmed to a second data state if the signal output by the memory cell is greater than the reference voltage.

[0016] If, however, the memory cell experiences threshold voltage drift, the threshold voltage value of the memory cell may change such that the signal output by the memory cell during a sense operation does not correspond to the data state to which the memory cell was programmed (e.g., is no longer the expected value of a signal output by a memory cell programmed to that data state). As used herein, "drift" refers to a difference between the programmed threshold voltage value of a memory cell and the sensed threshold voltage value of the memory cell. Threshold voltage drift can occur in a memory cell after multiple operations (e.g., multiple read cycles) are performed on the memory cell and/or due to temperature variations in the memory cell, for example. Threshold voltage drift can lead to an incorrect read in a memory cell. For instance, threshold voltage drift may result in the memory cells of a codeword being sensed to be in states to which they were not actually programmed (e.g., a cell programmed to be in the first data state may be erroneously sensed to be in the second data state, and/or vice versa). Such erroneous data sensing can reduce the performance and/or lifetime of the memory.

[0017] Embodiments of the present disclosure, however, can compensate for threshold voltage drift that may occur in the memory cells of a codeword, such that the data states of the memory cells of the codeword can be accurately determined. For example, embodiments of the present disclosure can use a Pearson detector to determine the originally programmed data of a codeword whose memory cells have been affected by threshold voltage drift. Accordingly, embodiments of the present disclosure can increase the performance and/or lifetime of memory that utilizes codewords (e.g., by estimating the original value of the data bits in a codeword that has been affected by threshold voltage drift.

[0018] As used herein, "a," "an," or "a number of" can refer to one or more of something, and "a plurality of" can refer to two or more such things. For example, a memory device can refer to one or more memory devices, and a plurality of memory devices can refer to two or more memory devices. Additionally, the designator "N", as used herein, particularly with respect to reference numerals in the drawings, indicates that a number of the particular feature so designated can be included with a number of embodiments of the present disclosure.

[0019] The figures herein follow a numbering convention in which the first digit or digits correspond to the drawing figure number and the remaining digits identify an element or component in the drawing. Similar elements or components between different figures may be identified by the use of similar digits.

[0020] FIGS. **1**A and **1**B illustrate diagrams of a number of threshold voltage (Vt) distributions, sensing voltages, and data assignments associated with a group of memory cells in accordance with an embodiment of the present disclosure. The group of memory cells can be, for example, a codeword, which can refer to a logical unit of a memory device used to store data. FIG. **1**A illustrates a diagram **103** of Vt distributions **110-1** and **110-2** associated with the data states of the memory cells of a codeword before the memory cells of the codeword have experienced threshold voltage drift, and FIG. **1**B illustrates a diagram **199** of Vt distributions **118-1** and **118-2** associated with codeword after the memory cells of the codeword have experienced threshold voltage drift.

[0021] As an example, the two Vt distributions **110-1** and **110-2** shown in FIG. **1**A, and the two Vt distributions **118-1** and **118-2** shown in FIG. **1**B, can correspond to single level (e.g., two-state) memory cells. However, embodiments of the present disclosure are not limited to single level memory cells. For example, embodiments of the present disclosure can include multilevel cells such as, for instance, triple level cells (TLCs), or quadruple level cells (QLCs). In such examples, the diagrams illustrated in FIGS. **1**A and **1**B would include additional Vt distributions (e.g., corresponding to each of the additional data states).

[0022] Vt distributions **110-1** and **110-2** shown in FIG. **1**A, and Vt distributions **118-1** and **118-2** shown in FIG. **1**B, represent two target data states (e.g., 1 and 0, respectively, which are represented in FIGS. **1**A and **1**B by −1 and 1, respectively) to which the memory cells of the group can be programmed. Embodiments of the present disclosure, however, are not limited to these data assignments.

[0023] Vt distributions **110-1** and **110-2** shown in FIG. **1**A, and Vt distributions **118-1** and **118-2** shown in FIG. **1**B, can represent a quantity (e.g., number) of memory cells of the group that are programmed to the corresponding target states (e.g., 1 and 0), with the height of a Vt distribution curve indicating the quantity of cells programmed to a particular voltage within the Vt distribution (e.g., on average). The width of the Vt distribution curve indicates the range of voltages that represent a particular target state (e.g., the width of the Vt distribution curves **110-2** and **118-2** represent the range of voltages that correspond to a data value of 0 for the original codeword (e.g. before the codeword has experienced threshold voltage drift) and the codeword after it has experienced threshold voltage drift, respectively). In the example illustrated in FIG. **1**A (e.g., the original codeword), the widths and heights of Vt distributions **110-1** and **110-2** are equivalent (e.g., equal). Further, in the example illustrated in FIG. **1**B (e.g., the codeword that has experienced drift), the widths and heights of Vt distributions **118-1** and **118-2** are equivalent.

[0024] During a sense (e.g., read) operation to determine the respective data states stored by the memory cells of the group, a reference voltage located between the two Vt distributions (e.g., at location 0 illustrated in FIG. **1**A) can be used to distinguish between the two data states (e.g., between states 1 and 0). For example, during a sense operation performed on a selected memory cell of the group, a sense voltage can be applied to first signal line (e.g., an access line) to which the memory cell is coupled, and the resulting voltage signal (e.g. in response to the sense voltage being applied to the access line) from the memory cell can be provided to sense circuitry via a second signal line (e.g., a sense line) to which the memory cell is coupled for comparison with the reference voltage. The data state for the selected memory cell can be determined using (e.g., by comparing) the voltage signal from that memory cell and the reference voltage.

[0025] In the examples illustrated in FIGS. **1**A and **1**B, the reference voltage used to distinguish between the two data states can be determined by averaging the threshold voltages of the memory cells of the group (e.g., codeword). For the original codeword (e.g., whose cells have not experienced threshold voltage drift), this reference voltage would be located exactly between its Vt distributions **110-1** and **110-2** at 0, as illustrated in FIG. **1**A. However, for the codeword whose memory cells have experienced drift, this reference voltage would be located exactly between its Vt distributions **118-1** and **118-2** at b instead of 0, which is illustrated in FIG. **1**B. As such, using 0 as the reference voltage to sense the data states of the memory cells of the codeword that has experienced drift may result in some cells of that codeword being sensed to be in a state to which they were not actually programmed to. For instance, a cell programmed to a target state of 1, but whose voltage is to the right of 0 (e.g., the reference voltage in FIG. **1**A) within distribution **118-1**, may be erroneously sensed to be in state 0.

[0026] Embodiments of the present disclosure, however, can compensate for this threshold voltage drift by determining (e.g., estimating) the original (e.g., expected) data bits of a codeword that has experienced threshold voltage drift. Estimating the originally programmed data of the codeword can reduce the likelihood of the data states of the memory cells in the codeword being read incorrectly when the memory cells have experienced threshold voltage drift.

[0027] FIG. **2** is a block diagram illustration of an example apparatus, such as an electronic memory system **200**, in accordance with an embodiment of the present disclosure. Memory system **200** may include an apparatus, such as a memory device **202** and a controller **204**, such as a memory controller (e.g., a host controller). Controller **204** might include a processor, for example. Controller **204** might be coupled to a host, for example, and may receive command signals (or commands), address signals (or addresses), and data signals (or data) from the host and may output data to the host.

[0028] Memory device **202** includes a memory array **201** of memory cells. For example, memory array **201** can include a group of memory cells, such as a codeword, as previously described herein (e.g., in connection with FIGS. **1**A-**1**B). Memory array **201** can be, for example, a DRAM array, such as, for instance, a ferroelectric memory (e.g., FeRAM) array. That is, the memory cells of array **201** can be DRAM (e.g., FeRAM) cells. However, embodiments are not limited to a particular type of memory array. For instance, in some embodiments, memory array **201** can be a NAND flash array (e.g., the memory cells of array **201** can be NAND flash memory cells). Further, although one memory array **201** is illustrated in FIG. **2** for simplicity and so as not to obscure embodiments of the present disclosure, memory device **202** can include a number of memory arrays analogous to array **201**.

[0029] Memory device **202** may include address circuitry **208** to latch address signals provided over I/O connections **211** through I/O circuitry **212**. Address signals may be received and decoded by a row decoder **214** and a column decoder **216** to access the memory array **201**. For example, row decoder **214** and/or column decoder **216** may include drivers.

[0030] Controller **204** may sense (e.g., read) data in memory array **201**, such as a codeword stored in array **201**, by using read/latch circuitry **221** and/or sensing circuitry **205**. Read/latch circuitry **221** may read and latch data from the memory array **201**. Sensing circuitry **205** may include a number of sense amplifiers coupled to memory cells of memory array **201**, which may operate in combination with the read/latch circuitry **221** to sense (e.g., read) memory states from targeted memory cells. I/O circuitry **212** may be included for bi-directional data communication over the I/O connections **211** with controller **204**. Write circuitry **222** may be included to program (e.g., write) data to memory array **201**.

[0031] Control circuitry **224** may decode signals provided by control connections **226** from controller **204**. These signals may include chip signals, write enable signals, and address latch signals that are used to control the operations on memory array **201**, including data read and data write operations. Control circuitry **224** may be included in controller **204**, for example. Controller **204** may include other circuitry, firmware, software, or the like, whether alone or in combination. Controller **204** may be an external controller (e.g., in a separate die from the memory array **201**, whether wholly or in part) or an internal controller (e.g., included in a same die as the memory array **201**). For example, an internal controller might be a state machine or a memory sequencer.

[0032] The memory device **202** can also include circuitry configured to determine (e.g., estimate) the originally programmed data of a codeword (e.g., a sensed codeword) that has experienced threshold voltage drift. For example, the memory device **202** can include sorting circuitry **207**, mean circuitry **209**, a Pearson detector **206**, parabolic term circuitry **213**, and proportional term circuitry **215**. The sorting circuitry **207** can sort the data bits (e.g., the threshold voltage values of the memory cells) of the codeword into different voltage distributions, the mean circuitry **209** can determine a mean threshold voltage value of the memory cells corresponding to the data bits in the codeword, the parabolic term circuitry **213** can determine a parabolic term of a codeword, proportional term circuitry **215** can determine a value proportional to the mean threshold voltage value of the codeword, and Pearson detector **206** can determine the originally programmed data of the codeword (e.g., the value of the data bits in the originally programmed codeword). In some embodiments, the sorting circuitry **207**, mean circuitry **209**, Pearson detector **206**, parabolic term circuitry **213**, and proportional term circuitry **215** can be included in (e.g., located on) a controller (e.g., controller **204**) instead of the memory device **202**. Mean circuitry **209**, parabolic term circuitry **213**, and proportional term circuitry **215** will be further described herein (e.g., in connection with FIGS. **4**, **5**, and **6**, respectively).

[0033] Determining the originally programmed data of a codeword includes inputting a cell metric determined to have the lowest value relative to the value of other cell metrics into the Pearson detector **206**. As used herein, the term "cell metric" refers to a value associated with a memory cell that can be input into a Pearson detector. In some embodiments, the value of the cell metric determined to have the lowest value and a correlation between a tentative codeword and the sensed codeword can be input into the Pearson detector to determine the originally programmed data of the codeword. As used herein, the term "tentative codeword" refers to a codeword that provides the lowest Pearson distance between the sensed codeword and the originally programmed codeword relative to the other

codewords in the memory array **201**. The sensed codeword can comprise a sensed data value of each of the memory cells of the sensed codeword. The originally programmed data of the codeword can include the programmed data value of each of the memory cells of the codeword (e.g., corresponding to the data bits in the originally programmed codeword).

[0034] The Pearson detector **206** can determine the originally programmed data of the codeword by searching for a codeword (e.g., a sensed codeword) that has a lowest Pearson distance from the original codeword relative to other codewords (e.g., other sensed codewords). As used herein, the term "Pearson distance" refers to a measure of the linear correlation between two sets of data (e.g. between two codewords). The Pearson detector can use the sensed codeword that has the lowest Pearson distance from the original codeword to estimate the value of each data bit of the original codeword. In some embodiments, the Pearson detector can determine the lowest Pearson distance using a weight estimator. The weight estimator can be the estimated weight of the original codeword. As used herein, the term "weight" refers to the number of data bits with a particular data value (e.g., the number bits with a value of 1) in a codeword.

[0035] In some embodiments, the weight estimator can be a value that minimizes the value of the cell metric. The value of the cell metric for each memory cell of the codeword can be determined based on a summation of the threshold voltage value of each of the memory cells, the mean of the threshold voltage values of the memory cells, and a value proportional to the mean of the threshold voltage values of the memory cells. For example, the value of the cell metric for each memory cell (e.g., each data bit) in the sensed codeword can be determined by the following equation:

$$\delta_w(Y) = \sum_{i=1}^{w} (Y_{i:N}) + \frac{w(N-w)}{N} - \mu_Y w$$

In the foregoing equation, the cell metric for each respective memory cell is represented by the symbol $\delta_w(Y)$. The equation states that the cell metric can be determined by adding the sum of the sorted threshold voltage values of each of the memory cells in the sensed codeword, represented in the foregoing equation as $\Sigma_{i=1}^{w}(Y_{i:N})$, to a parabolic term, represented in the foregoing equation as

$$\frac{w(N-w)}{N},$$

and subtracting a term proportional to the mean μ_y, represented in the foregoing equation as $\mu_y w$. In some embodiments, the value of the parabolic term can be accessed from a lookup table or by an analog circuit, as will be further described herein. The "w" in the foregoing equation can denote the position of a data bit in the sensed codeword (e.g., the position of the threshold voltage value of the memory cell corresponding to the data bit in the sorted threshold voltage values), and "N" can denote the total quantity of memory cells of the codeword. For example, if w has a value of 5, that can indicate that the equation will find the cell metric value for the fifth data bit in the sensed codeword (e.g., for the memory cell whose threshold voltage value is fifth in the sorted threshold voltage values). The cell metric with the lowest value can be the weight estimator. The weight estimator can be input into the Pearson detector **206** to determine the originally programmed data of the codeword. The process for sorting the data bits (e.g., the threshold voltage values of the memory cells) of the sensed codeword in ascending order (e.g., based on the threshold voltage value of the corresponding memory cell) is described in connection with FIG. **3** and the process for determining the mean of the sorted threshold voltage values is described in connection with FIG. **4**. Further, the process for determining the parabolic term is described in connection with FIG. **5** and the process for determining the term proportional to the mean of the threshold voltage values is described in connection with FIG. **6**. The process for determining the cell metric can be performed by digital or analog processing mechanisms.

[0036] The number of data bits in the codeword having a value of 0 can be different than the number of data bits in that same codeword that have a value of 1. In some embodiments, a data bit that has a first value can be added to the codeword if the sensed codeword only comprises data bits having a second value. For example, if the codeword only comprises data bits having a value of 1, a data bit with a value of 0 can be added to the codeword. Alternatively, if the codeword only comprises data bits having a value of 0, a data bit with a value of 1 can be added to the codeword.

[0037] FIG. **3** is a diagram illustrating voltage distributions and corresponding data bits in a codeword in accordance with an embodiment of the present disclosure. FIG. **3** illustrates a diagram **320** including a ramp voltage **328**, switching event times **330-1**, **330-2**, . . . , **330**-N (individually or collectively referred to as switching event times **330**) of data bits **334-1**, **334-2**, . . . , **334**-N (individually or collectively referred to as data bits **334**) in a codeword **332**. The diagram **320** also includes voltage distributions **336-1** and **336-2**.

[0038] Diagram **320** includes switching event times **330** for data bits **334** of a codeword **332** (e.g., switching event time **330-1** for data bit **334-1**, switching event time **330-2** for data bit **334-2**, etc.). As used herein, the term "switching event" refers to an occurrence of a memory cell changing from a low conductive state to a high conductive state, or a high conductive state to a low conductive state, in response to receiving a current that has a voltage that is greater than or equal to the threshold voltage of the memory cell. In some embodiments, applying the ramped up voltage **328** (e.g., a voltage that increases with time) to each of the memory cells can initiate a switching event in each of the memory cells at different times. For instance, in the example illustrated in FIG. **3**, the memory cell of the codeword corresponding to data bit **334-1** (e.g., $Y_{1:N}$) is the first cell to switch (at switching event time **330-1**), the memory cell of the codeword corresponding to data bit $Y_{2:N}$ is the second cell to switch (at switching event time **330-2**), and the memory cell of the codeword corresponding to data bit **334-2** is the fifth cell to switch. The threshold voltage value of each of the memory cells can be determined after the switching event occurs in that respective memory cell.

[0039] In some embodiments, circuitry (e.g., sorting circuitry **207** in FIG. **2**) can sort the threshold voltage values of each of the memory cells in ascending order (e.g., from lowest to highest). Further, the sorted threshold voltage values can be divided into a first distribution **336-1** and

second distribution **336-2**, with the first distribution including the lower threshold voltage values (e.g., the cells of the codeword with the shorter switching times) and the second distribution including the higher threshold voltage values (e.g., the cells of the codeword with the longer switching times). In some embodiments, the sorted threshold voltages are divided into the first distribution **336-1** and the second distribution **336-2** such that the quantity of threshold voltage values in the first distribution **336-1** is equal to an estimated weight of the codeword **332**. Further, the sorted threshold voltage values can be divided into the first distribution **336-1** and the second distribution **336-2** such that the quantity of the threshold voltage values in the second distribution **336-2** is equal to a difference between the quantity of memory cells in the codeword **332** and the quantity of the threshold voltage values in the first distribution **336-1**.

[0040] FIG. **4** illustrates circuitry **409** for determining the mean threshold voltage value of memory cells corresponding to data bits in a codeword in accordance with an embodiment of the present disclosure. Circuitry **409** can be, for instance, circuitry **209** previously described in connection with FIG. **2**. As shown in FIG. **4**, circuitry **409** includes a mean voltage line **429**, a ramp voltage line **428**, switches **438-1**, **438-2**, **438-3**, . . . , **438**-N (individually or collectively referred to as switches **438**), connectors **442-1-1**, **442-1-2**, **442-1-3**, . . . , **442**-N-**1**, **442**-N-**2**, and **442**-N-**3** (individually or collectively referred to as connectors **442**), and capacitors **440-1**, **440-2**, **440-3**, . . . , **440**-N (individually or collectively referred to as capacitors **440**).

[0041] Each respective one of the plurality of switches **438** can be configured to couple a different one of the memory cells of memory array **201** previously described in connection with FIG. **2** to a different one of a plurality of connectors **442**. The ramped voltage line **428** can output a ramped voltage (e.g., ramped voltage **328** previously described in connection with FIG. **3**), and each of the memory cells can be coupled to the ramped voltage via the ramp voltage line **428** when its respective switch **438** is coupled to a first connector **442-1-1**, **442-2-1**, **442-3-1**, . . . , **442**-N-**1** of the plurality of connectors **442** (e.g., the memory cell coupled to switch **438-1** can be coupled to ramp voltage line **428** when switch **438-1** is coupled to first connector **442-1-1**, the memory cell coupled to switch **438-2** can be coupled to ramp voltage line **428** when switch **438-2** is coupled to first connector **442-2-1**, etc.). In some embodiments, each of the plurality of switches **438** can be coupled to its respective first connector (e.g., to the ramp voltage line **428**) until its corresponding memory cell reaches its threshold voltage. Each memory cell that is coupled to the ramp voltage line **428** may experience a switching event when it reaches its threshold voltage.

[0042] In some embodiments, each respective one of the plurality of switches **438** can be configured to decouple from the first connector **442-1-1**, **442-2-1**, **442-3-1**, . . . , **442**-N-**1** and couple to a second connector **442-1-2**, **442-2-2**, **442-3-2**, . . . , **442**-N-**2** of the plurality of connectors once its respective memory cell experiences a switching event (e.g., switch **438-1** can decouple from first connector **442-1-1** and couple to second connector **442-1-2** once the memory cell coupled to switch **438-1** experiences a switching event, switch **438-2** can decouple from first connector **442-2-1** and couple to second connector **442-2-2** once the memory cell coupled to switch **438-2** experiences a switching event, etc.). In some embodiments, the switches **438** can couple to the second connector **442-1-2**, **442-2-2**, **442-3-2**, . . . , **442**-N-**2** to store the voltage level of the corresponding memory cells (e.g., the threshold voltage of the cells when they experience the switching event) in capacitors **440**. For example, once the memory cell that is coupled to switch **438-1** reaches its threshold voltage and experiences a switching event, switch **438-1** can decouple from the first connector **442-1-1** and couple to the second connector **442-1-2** to store the voltage of that memory cell in capacitor **440-1**, while the other switches **438** can remain connected to their respective first connector.

[0043] In some embodiments, each respective one of the plurality of switches **442** can be configured to decouple form the second connector **442-1-2**, **442-2-2**, **442-3-2**, . . . , **442**-N-**2** and couple to a third connector **442-1-3**, **442-2-3**, **442-3-3**, . . . , **442**-N-**3** of the plurality of connectors once each (e.g., every) memory cell experiences a switching event. As shown in FIG. **4**, coupling the switches **438** to the third connector **442-1-3**, **442-2-3**, **442-3-3**, . . . , **442**-N-**3** couples the switches **438**, and therefore the capacitors **440**, to the mean voltage line **429**. In some embodiments, each of the plurality of switches **438** can be configured to couple to its respective third connector **442-1-3**, **442-2-3**, **442-3-3**, . . . , **442**-N-**3** simultaneously. In some embodiments, each of the memory cells can be coupled to a common node when each of the plurality of switches **438** is coupled to its respective third connector **442-1-3**, **442-2-3**, **442-3-3**, . . . , **442**-N-**3**.

[0044] Controller **204** and/or control circuitry **224** previously described in connection with FIG. **2** can be configured to determine the mean of the threshold voltage values of the memory cells when each of the plurality of switches **438** is coupled to its respective third connector **442-1-3**, **442-2-3**, **442-3-3**, . . . , **442**-N-**3**. The controller and/or control circuitry can determine the mean of the threshold voltage values of the memory cells by measuring the total voltage value stored by the capacitors **440** coupled to the mean voltage line **429** and dividing that value by the number of memory cells.

[0045] FIG. **5** illustrates circuitry **513** for determining a parabolic term of a codeword in accordance with an embodiment of the present invention. Circuitry **513** can be, for example, parabolic term circuitry **213** previously described in connection with FIG. **2**. The parabolic term circuitry **513** can include a plurality of resistors **548-1**, **548-1**, . . . , **548**-N (individually or collectively referred to as resistors **548**) coupled in series, a current (e.g., current supply) **544**, and a node **546** between two of the resistors **548**.

[0046] The current **544** can be applied to node **546**. In the embodiment shown in FIG. **5**, the current **544** is applied to the node **546** between resistors **548-3** and **548-4**. However, the current **544** can be applied to a node **546** between any two adjacent resistors **548**. In some embodiments, each resistor **548** can correspond to a data bit (e.g., data bit **334** in FIG. **3**) in a codeword (e.g., codeword **332** in FIG. **3**). In the embodiment shown in FIG. **5**, resistor **548-3** corresponds to a third data bit in the codeword and resistor **548-4** corresponds to a fourth data bit in the codeword. In some embodiments, the parabolic term circuitry **513** can include transistors instead of resistors **548**.

[0047] In some embodiments, the value of the voltage at the node **546** when the current **544** is applied to the node **546** can be determined via the equation **550**. The equation **550** states the value of the voltage at the node **546** can be found

by multiplying a resistance R of a resistor **548** corresponding to the node by the value I of the current **544**. The value of that operation can be multiplied by the value of an operation that multiplies the number i of resistors **548** before the node **546** (e.g., the node to which the current **544** was applied) in the series of resistors to the number N-i of resistors **548** after the node **546** in the series of resistors and divides that value by the number of data bits N (e.g., the number of memory cells) in the corresponding codeword. The parabolic term can be found by determining the value of the voltage at each node between the resistors **548** when the current **544** is applied to each node **546**.

[0048] FIG. **6** illustrates circuitry **615** for determining a term proportional to the mean threshold voltage value of memory cells corresponding to data bits of a codeword in accordance with an embodiment of the present invention. Circuitry **615** can be, for example, proportional term circuitry **215** previously described in connection with FIG. **2**. The proportional term circuitry **615** can include a buffer **652**, a plurality of resistors **654-1** and **654-2**, and a plurality of capacitors **656-1**, **656-2**, . . . , **656**-N.

[0049] In some embodiments, the proportional term circuitry **615** can be used to determine a value that is proportional to the mean of the threshold voltage values. The value proportional to the mean can be determined by inputting the mean of threshold voltages values into the buffer **652**. In some embodiments, the first resistor **654-1** can be coupled to an input of the buffer **652** and a second resistor **654-2** is coupled to first resistor **654-1** and an output of the buffer **652**. Further, in some embodiments, the buffer **652** can output a voltage to each of a plurality of nodes **658-1**, **658-2**, . . . , **658**-N (individually or collectively referred to as nodes **658**) that couple each of the plurality of capacitors **656** (e.g., node **658-2** couples capacitors **656-1** and **656-2**, node **658-3** couples capacitors **656-2** and **656-3**, etc.).

[0050] As shown in FIG. **6**, the proportional term circuitry **615** can be configured such that the output of the buffer **652** is equal to the mean threshold voltage value of the memory cells corresponding to data bits in the codeword (e.g., the mean threshold voltage value determined by mean circuitry **409** described in connection with FIG. **4**) multiplied by the result of an operation that adds a value of 1 to the quotient of the resistance R_2 of the second resistor **654-2** divided by the resistance R_1 of the first resistor **654-1**. In some embodiments, the result of this operation can be equal to the number of data bits in the codeword. As represented by nodes **658-1**, . . . , **658**-(N-**2**), **658**-(N-**1**), **658**-N, the term proportional to the mean can be found for each data bit in the codeword. For example, the term proportional to the mean can be found for the last data bit in the codeword at node **658**-N. Further, the term proportional to the mean for the first data bit can be found at node **658-1**.

[0051] Although specific embodiments have been illustrated and described herein, those of ordinary skill in the art will appreciate that an arrangement calculated to achieve the same results can be substituted for the specific embodiments shown. This disclosure is intended to cover adaptations or variations of a number of embodiments of the present disclosure. It is to be understood that the above description has been made in an illustrative fashion, and not a restrictive one. Combination of the above embodiments, and other embodiments not specifically described herein will be apparent to those of ordinary skill in the art upon reviewing the above description. The scope of a number of embodiments of the present disclosure includes other applications in which the above structures and methods are used. Therefore, the scope of a number of embodiments of the present disclosure should be determined with reference to the appended claims, along with the full range of equivalents to which such claims are entitled.

[0052] In the foregoing Detailed Description, some features are grouped together in a single embodiment for the purpose of streamlining the disclosure. This method of disclosure is not to be interpreted as reflecting an intention that the disclosed embodiments of the present disclosure have to use more features than are expressly recited in each claim. Rather, as the following claims reflect, inventive subject matter lies in less than all features of a single disclosed embodiment. Thus, the following claims are hereby incorporated into the Detailed Description, with each claim standing on its own as a separate embodiment.

What is claimed is:

1. An apparatus, comprising:

a memory device, comprising:

an array of memory cells; and

circuitry configured to:

sense a codeword stored in the array of memory cells;

determine a value of a cell metric of each memory cell of the sensed codeword, wherein the value of the cell metric of each of the memory cells is determined based on:

a summation of a threshold voltage value of each of the memory cells;

a mean of the threshold voltage values of the memory cells; and

a value proportional to the mean of the threshold voltage values of the memory cells;

determine which cell metric of each of the memory cells has a lowest value;

input the cell metric determined to have the lowest value to a Pearson detector; and

determine originally programmed data of the codeword using the Pearson detector.

2. The apparatus of claim **1**, wherein the value of the cell metric determined to have the lowest value and a correlation between a tentative codeword and the sensed codeword are input into the Pearson detector to determine the originally programmed data of the codeword.

3. The apparatus of claim **1**, wherein the sensed codeword comprises a sensed data value of each of the memory cells of the sensed codeword.

4. The apparatus of claim **1**, wherein the originally programmed data of the codeword comprises a programmed data value of each of the memory cells of the codeword.

5. A method, comprising:

sensing a codeword stored in an array of memory cells of a memory device;

determining, by the memory device, for each memory cell of the sensed codeword, a value of a cell metric of each of the memory cells of the sensed codeword, wherein the value of the cell metric of each of the memory cells of the sensed codeword is determined based on:

a summation of a threshold voltage value of each of the memory cells;

a mean of the threshold voltage values of the memory cells; and

a value proportional to the mean of the threshold voltage values of the memory cells;

determining, by the memory device, which cell metric of each of the memory cells has a lowest value;

inputting the cell metric determined to have the lowest value to a Pearson detector; and

determining originally programmed data of the codeword using the Pearson detector.

6. The method of claim **5**, further comprising determining the threshold voltage value of each of the memory cells after a switching event occurs in each of the memory cells.

7. The method of claim **6**, further comprising initiating the switching event in each of the memory cells by applying a ramped voltage to the memory cells.

8. The method of claim **5**, further comprising sorting the threshold voltage values of each of the memory cells in ascending order.

9. The method of claim **8**, further comprising dividing the sorted threshold voltage values into a first distribution and a second distribution.

10. The method of claim **9**, wherein the sorted threshold voltage values are divided into the first distribution and the second distribution such that a quantity of the threshold voltage values in the first distribution is equal to an estimated weight of the codeword.

11. The method of claim **9**, wherein the sorted threshold voltage values are divided into the first distribution and the second distribution such that a quantity of the threshold voltage values in the second distribution is equal to a difference between a quantity of memory cells in the codeword and a quantity of the threshold voltage values in the first distribution.

12. An apparatus, comprising:

a memory device comprising an array of memory cells; and

a controller coupled to the memory device and configured to:

sense a codeword stored in the array of memory cells;

determine, for each memory cell of the sensed codeword in the memory device, a value of a cell metric of each of the memory cells of the sensed codeword, wherein the value of the cell metric of each of the memory cells of the codeword is determined based on:

a summation of a threshold voltage value of each of the memory cells;

a mean of the threshold voltage values of the memory cells; and

a value proportional to the mean of the threshold voltage values of the memory cells;

determine which cell metric of each of the memory cells has a lowest value; and

input the cell metric determined to have the lowest value to a Pearson detector; and

determine originally programmed data of the codeword using the Pearson detector.

13. The apparatus of claim **12**, wherein the Pearson detector determines the originally programmed data of the codeword by searching for a codeword that has a lowest Pearson distance from the codeword relative to other codewords.

14. The apparatus of claim **13**, wherein the Pearson detector determines the lowest Pearson distance using a weight estimator.

15. The apparatus of claim **12**, wherein the memory device includes a plurality of switches, wherein each respective one of the plurality of switches is configured to couple a different one of the memory cells to a different one of a plurality of connectors.

16. The apparatus of claim **15**, wherein each of the memory cells is coupled to a ramped voltage when its respective switch is coupled to a first connector of the plurality of connectors.

17. The apparatus of claim of claim **16**, wherein each respective one of the plurality of switches is configured to decouple from the first connector and couple to a second connector of the plurality of connectors once its respective memory cell experiences a switching event.

18. The apparatus of claim **17**, wherein each respective one of the plurality of switches is configured to decouple from the second connector and couple to a third connector when each of the plurality of memory cells experiences the switching event.

19. The apparatus of claim **18**, wherein each of the plurality of memory cells is coupled to a common node when each of the plurality of switches is coupled to its respective third connector.

20. The apparatus of claim **18**, wherein the controller is configured to determine the mean of the threshold voltage values of the memory cells when each of the plurality of switches is coupled to its respective third connector.

21. The apparatus of claim **18**, wherein each of the plurality of switches are configured to couple to its respective third connector simultaneously.

22. A method, comprising:

sensing a codeword stored in an array of memory cells of a memory device;

determining, by a controller coupled to the memory device, for each memory cell of a sensed codeword in the memory device, a value of a cell metric of each memory cell of the codeword, wherein the value of the cell metric of each memory cell of the codeword is based on:

a summation of a threshold voltage value of each of the memory cells;

a mean of the threshold voltage values of the memory cells; and

a value proportional to the mean of the threshold voltage values of the memory cells;

determining, by the controller, which cell metric of each of the memory cells has a lowest value;

inputting the cell metric determined to have the lowest value to a Pearson detector; and

determining originally programmed data of the codeword using the Pearson detector.

23. The method of claim **22**, further comprising determining the value proportional to the mean of the threshold voltage values via circuitry that comprises a buffer, a plurality of resistors, and a plurality of capacitors.

24. The method of claim **23**, wherein the method includes determining the value proportional to the mean of the threshold voltage values by inputting the mean of the threshold voltage values into the buffer, wherein:

a first resistor is coupled to an input of the buffer and a second resistor is coupled to an output of the buffer; and

the buffer outputs a voltage to each of a plurality of nodes that couple each of the plurality of capacitors.

25. The method of claim **21**, further comprising adding a data bit having a first value to the codeword if the sensed codeword only comprises data bits having a second value.

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